



ZXTP19060CZ

60V PNP medium transistor in SOT89

Summary

$BV_{CEO} > -60V$

$BV_{ECO} > -7V$

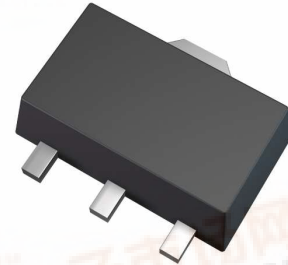
$I_{C(cont)} = 4.5A$

$V_{CE(sat)} < -80mV @ -1A$

$R_{CE(sat)} = 50m\Omega$

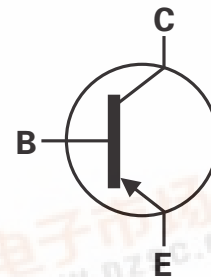
$P_D = 2.4W$

Complementary part number ZXTN19060CZ



Description

Packaged in the SOT89 outline this new low saturation PNP transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.



Features

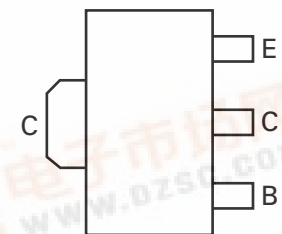
- High gain
- Low saturation voltage
- High peak current
- 7V reverse blocking voltage

Applications

- High side driver
- Motor drive
- Load disconnect switch

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP19060CZTA	7	12	1000



Pinout - top view

Device marking

1M2



ZXTP19060CZ

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-Base voltage	V_{CBO}	-60	V
Collector-Emitter voltage	V_{CEO}	-60	V
Emitter-Collector voltage (reverse blocking)	V_{ECX}	-7	V
Emitter-Base voltage	V_{EBO}	-7	V
Continuous Collector current ^(c)	I_C	-4.5	A
Base current	I_B	-1	A
Peak pulse current	I_{CM}	-7	A
Power dissipation at $T_A = 25^\circ\text{C}^{(a)}$	P_D	1.1	W
Linear derating factor		8.8	mW/°C
Power dissipation at $T_A = 25^\circ\text{C}^{(b)}$	P_D	1.8	W
Linear derating factor		14.4	mW/°C
Power dissipation at $T_A = 25^\circ\text{C}^{(c)}$	P_D	2.4	W
Linear derating factor		19.2	mW/°C
Power dissipation at $T_A = 25^\circ\text{C}^{(d)}$	P_D	4.46	W
Linear derating factor		35.7	mW/°C
Power dissipation at $T_C = 25^\circ\text{C}^{(e)}$	P_D	26.7	W
Linear derating factor		213	mW/°C
Operating and storage temperature range	T_j, T_{stg}	-55 to 150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	117	°C/W
Junction to ambient ^(b)	$R_{\theta JA}$	68	°C/W
Junction to ambient ^(c)	$R_{\theta JA}$	51	°C/W
Junction to ambient ^(d)	$R_{\theta JA}$	28	°C/W
Junction to case ^(e)	$R_{\theta JC}$	4.69	°C/W

NOTES:

(a) For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) Mounted on 25mm x 25mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

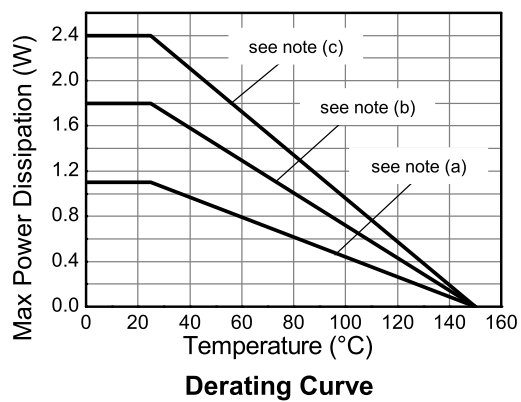
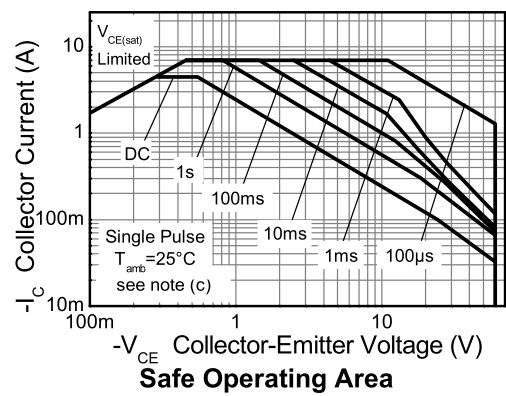
(c) Mounted on 50mm x 50mm x 0.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.

(d) As (c) above measured at $t < 10$ seconds.

(e) Junction to case (collector tab). Typical

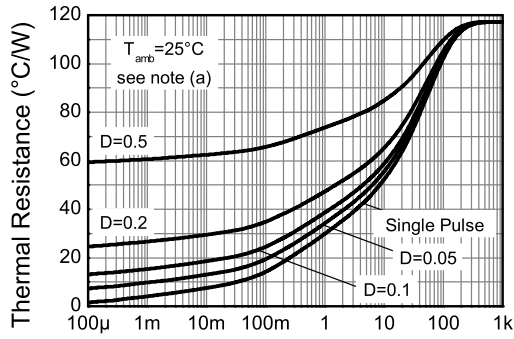
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Thermal characteristics

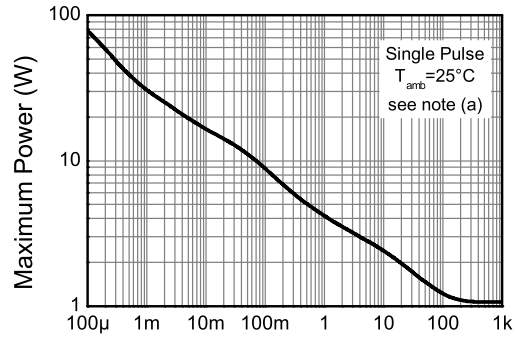


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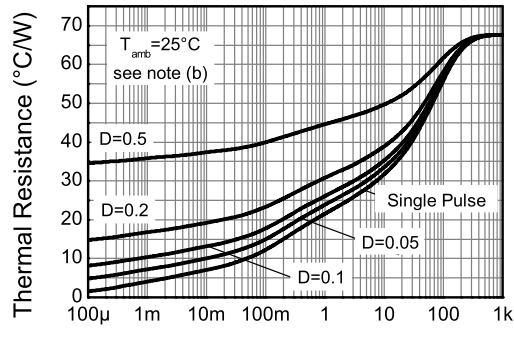
Thermal characteristics



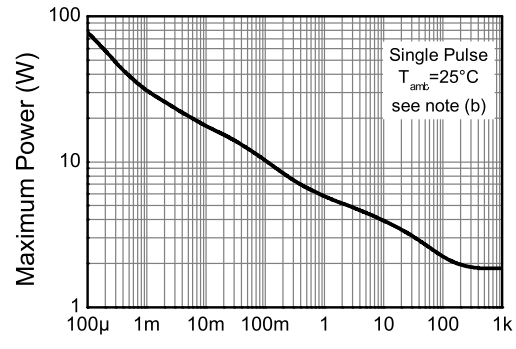
Transient Thermal Impedance



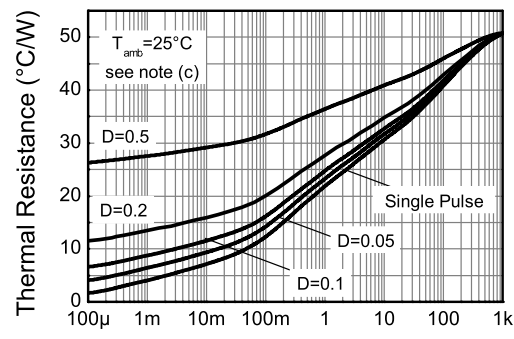
Pulse Power Dissipation



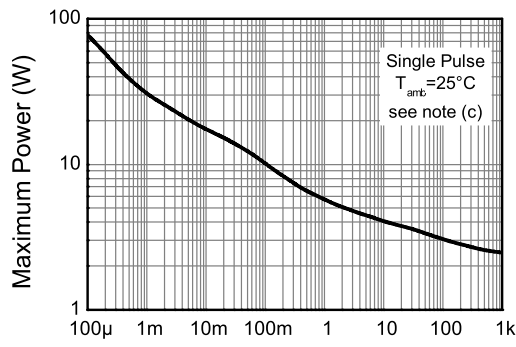
Transient Thermal Impedance



Pulse Power Dissipation



Transient Thermal Impedance



Pulse Power Dissipation

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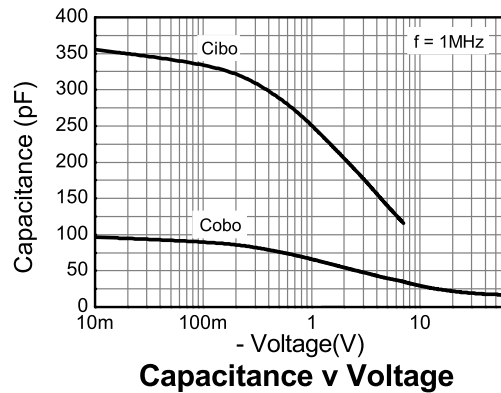
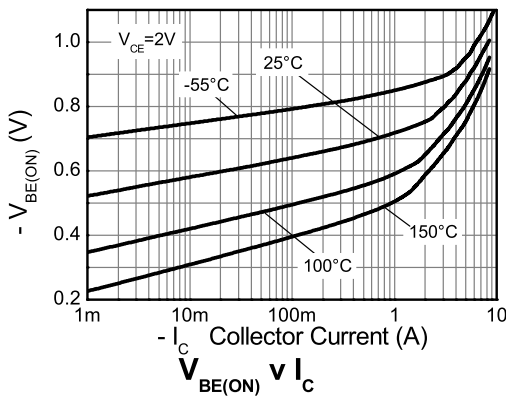
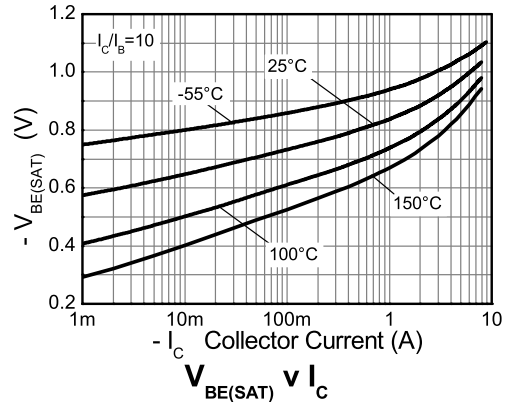
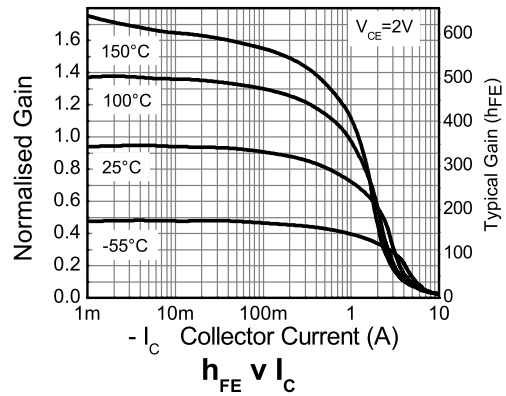
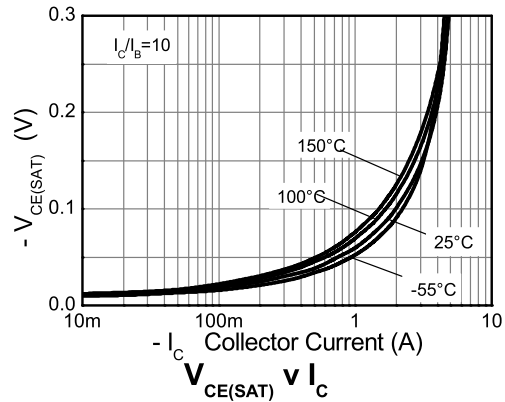
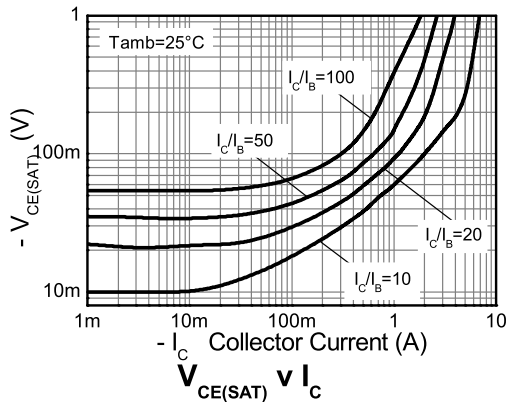
Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-Base breakdown voltage	BV_{CBO}	-60	-110		V	$I_C = -100\mu\text{A}$
Collector-Emitter breakdown voltage	BV_{CEO}	-60	-90		V	$I_C = -10\text{mA}^{(*)}$
Emitter-Collector breakdown voltage (reverse blocking)	BV_{ECX}	-7	-8.4		V	$I_E = -100\mu\text{A}$, $R_{BC} < 1\text{k}\Omega$ or $0.25\text{V} > V_{BC} > -0.25\text{V}$
Emitter-Collector breakdown voltage (reverse blocking)	BV_{ECO}	-7	-8.8		V	$I_E = -100\mu\text{A}$
Emitter-Base breakdown voltage	BV_{EBO}	-7	-8.4		V	$I_E = -100\mu\text{A}$
Collector-Base cut-off current	I_{CBO}		<1	-50 -0.5	nA μA	$V_{CB} = -60\text{V}$ $V_{CB} = -60\text{V}$, $T_{amb}=100^{\circ}\text{C}$
Emitter cut-off current	I_{EBO}		<1	-50	nA	$V_{EB} = -5.6\text{V}$
Collector-Emitter saturation voltage	$V_{CE(sat)}$		-62 -150 -500 -105 -145 -240	-80 -205 -750 -165 -200 -410	mV mV mV mV mV mV	$I_C = -1\text{A}$, $I_B = -100\text{mA}^{(*)}$ $I_C = -1\text{A}$, $I_B = -20\text{mA}^{(*)}$ $I_C = -2\text{A}$, $I_B = -40\text{mA}^{(*)}$ $I_C = -2\text{A}$, $I_B = -200\text{mA}^{(*)}$ $I_C = -3\text{A}$, $I_B = -300\text{mA}^{(*)}$ $I_C = -4.5\text{A}$, $I_B = -450\text{mA}^{(*)}$
Base-Emitter saturation voltage	$V_{BE(sat)}$		-965	-1050	mV	$I_C = -4.5\text{A}$, $I_B = -450\text{mA}^{(*)}$
Base-Emitter turn-on voltage	$V_{BE(on)}$		-875	-1000	mV	$I_C = -4.5\text{A}$, $V_{CE} = -2\text{V}^{(*)}$
Static forward current transfer ratio	h_{FE}	200 160 25	330 260 45	500		$I_C = -100\text{mA}$, $V_{CE} = -2\text{V}^{(*)}$ $I_C = -1\text{A}$, $V_{CE} = -2\text{V}^{(*)}$ $I_C = -4.5\text{A}$, $V_{CE} = -2\text{V}^{(*)}$
Transition frequency	f_T		180		MHz	$I_C = -50\text{mA}$, $V_{CE} = -10\text{V}$ $f = 50\text{MHz}$
Input capacitance	C_{ibo}		280	400	pF	$V_{EB} = -0.5\text{V}$, $f = 1\text{MHz}^{(*)}$
Output capacitance	C_{obo}		29.5	40	pF	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}^{(*)}$
Delay time	t_d		24.3		ns	$I_C = -500\text{mA}$, $V_{CC} = -10\text{V}$, $I_{B1} = -I_{B2} = -50\text{mA}$
Rise time	t_r		13.2		ns	
Storage time	t_s		456		ns	
Fall time	t_f		68.2		ns	

NOTES:

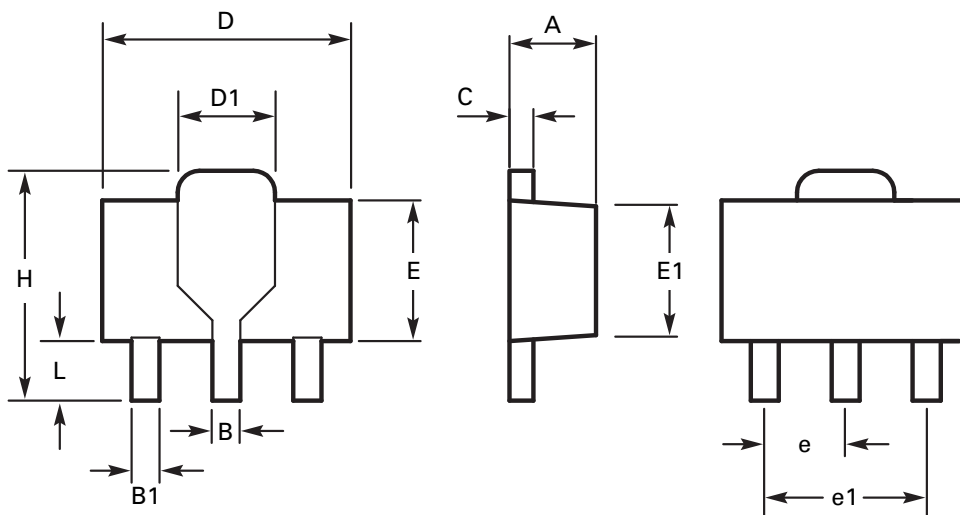
(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

Typical characteristics



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Package outline - SOT89



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.40	1.60	0.550	0.630	E	2.29	2.60	0.090	0.102
B	0.44	0.56	0.017	0.022	E1	2.13	2.29	0.084	0.090
B1	0.36	0.48	0.014	0.019	e	1.50 BSC		0.059 BSC	
C	0.35	0.44	0.014	0.017	e1	3.00 BSC		0.118 BSC	
D	4.40	4.60	0.173	0.181	H	3.94	4.25	0.155	0.167
D1	1.52	1.83	0.064	0.072	L	0.89	1.20	0.035	0.047

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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